

# HRF32

## Silicon Schottky Barrier Diode for High Frequency Rectifying

# HITACHI

Rev. 3  
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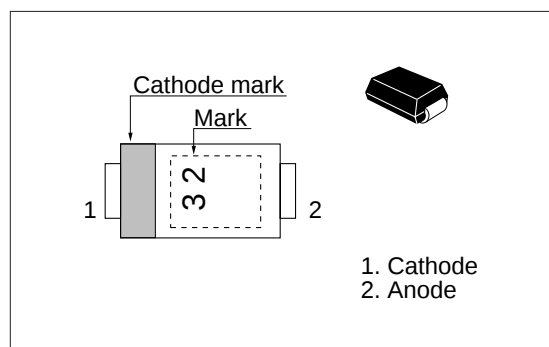
### Features

- Good for high-frequency rectify for  $V_R=90V$ ,  $I_o=1.0A$ , Output voltage=12Vmax.
- LRP structure ensures higher reliability.

### Ordering Information

| Type No. | Lazer Mark | Package Code |
|----------|------------|--------------|
| HRF32    | 32         | LRP          |

### Outline



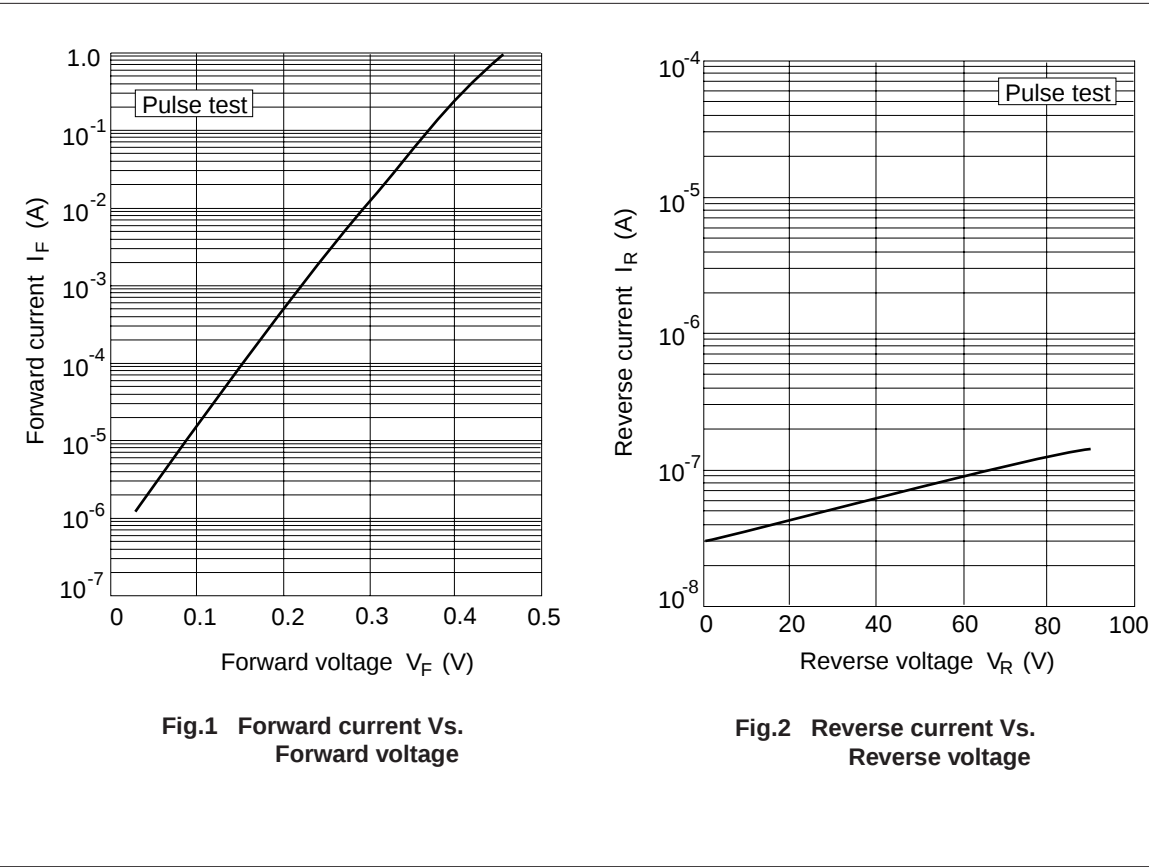
### Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

| Item                                      | Symbol      | Value       | Unit       |
|-------------------------------------------|-------------|-------------|------------|
| Repetitive peak reverse voltage           | $V_{RRM}$   | 90          | V          |
| Average forward current                   | $I_o$       | 1.0         | A          |
| Non-Repetitive peak forward surge current | $I_{FSM}^*$ | 20          | A          |
| Junction temperature                      | $T_j$       | 125         | $^\circ C$ |
| Storage temperature                       | $T_{stg}$   | -40 to +125 | $^\circ C$ |

\* 10msec sine wave 1 pulse

### Electrical Characteristics ( $T_a = 25^\circ C$ )

| Item            | Symbol | Min | Typ | Max | Unit | Test Condition                                                      |
|-----------------|--------|-----|-----|-----|------|---------------------------------------------------------------------|
| Forward voltage | $V_F$  | —   | —   | 0.8 | V    | $I_F = 1.0 A$                                                       |
| Reverse current | $I_R$  | —   | —   | 1.0 | mA   | $V_R = 90 V$                                                        |
| ESD-Capability  | —      | 150 | —   | —   | V    | *C=200pF R=0 $\Omega$<br>Both forward and reversedirection 1 pulse. |



Package Dimensions

Unit: mm

